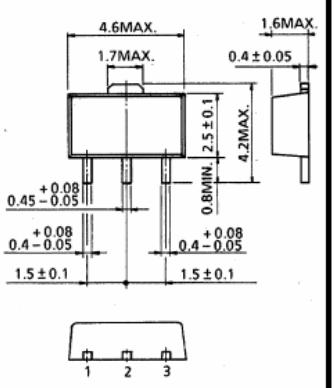
2SK3078

900 MHz BAND AMPLIFIER APPLICATIONS (GSM)

2SK3078 products listed in this document are intended for high frequency Power Amplifier of telecommunications equipment.

- Output Power : P_O = 27.0 dBmW (Min.)
- Gain : G_P = 12.5 dB (Min.)
- Drain Efficiency : η_D = 46% (Typ.)

Unit: mm



1. GATE
2. SOURCE
3. DRAIN

JEDEC	—
JEITA	SC-62

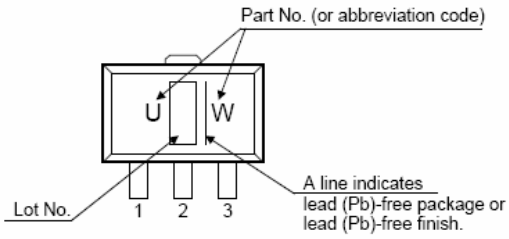
ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	10	V
Gate-Source Voltage	V_{GSS}	5	V
Drain Current	I_D	0.5	A
Power Dissipation	P_D (Note 1)	3.0	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	−45~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Tc = 25°C When mounted on a 1.6 mm glass epoxy PCB

MARKING



1. Gate
2. Source
3. Drain

Caution: This device is sensitive to electrostatic discharge.
Please make enough tool and equipment earthed when you handle.